

Very Low Forward Voltage Trench-based Schottky Rectifier

NRVTS2H60ESF, NRVTSM260EV2

Features

- Fine Lithography Trench-based Schottky Technology for Very Low Forward Voltage and Low Leakage
- Fast Switching with Exceptional Temperature Stability
- Low Power Loss and Lower Operating Temperature
- Higher Efficiency for Achieving Regulatory Compliance
- Low Thermal Resistance
- High Surge Capability
- NRV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

Mechanical Characteristics:

- Case: Molded Epoxy
- Epoxy Meets UL 94 V-0 @ 0.125 in
- Weight: 11.7 mg (Approximately)
- Lead and Mounting Surface Temperature for Soldering Purposes: 260°C Maximum for 10 Seconds
- MSL 1

Typical Applications

- Switching Power Supplies including Compact Adapters and Flat Panel Display
- High Frequency and DC-DC Converters
- Freewheeling and OR-ing diodes
- Reverse Battery Protection
- Instrumentation

TRENCH SCHOTTKY RECTIFIER 2.0 AMPERES 60 VOLTS

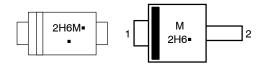




SOD-123FL CASE 498

POWERMITE CASE 457

MARKING DIAGRAMs



2H6 = Specific Device Code
M = Date Code
Device Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

Device	Package	Shipping [†]
NRVTS2H60ESFT1G	SOD-123FL (Pb-Free)	3,000 / Tape & Reel
NRVTS2H60ESFT3G	SOD-123FL (Pb-Free)	10,000 / Tape & Reel
NRVTSM260EV2T1G	Powermite (Pb-Free)	3,000 / Tape & Reel
NRVTSM260EV2T3G	Powermite (Pb-Free)	12,000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

NRVTS2H60ESF, NRVTSM260EV2

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V _{RRM} V _{RWM} V _R	60	V
Average Rectified Forward Current (T _L = 125°C)	lo	2.0	Α
Peak Repetitive Forward Current (Square Wave, 20 kHz, T _L = 139°C)	I _{FRM}	4.0	Α
Non-Repetitive Peak Surge Current (Surge Applied at Rated Load Conditions Halfwave, Single Phase, 60 Hz)	I _{FSM}	50	Α
Storage and Operating Junction Temperature Range (Note 1)	T _{stg} , T _J	-65 to +175	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS

Characteristic	Symbol	Value	Unit
SOD-123FL	•		
Thermal Resistance, Junction-to-Lead (Note 2)	Ψ_{JCL}	24.4	°C/W
Thermal Resistance, Junction-to-Ambient (Note 2)	$R_{ hetaJA}$	85	°C/W
Thermal Resistance, Junction-to-Ambient (Note 3)	$R_{ hetaJA}$	330	°C/W
POWERMITE			
Thermal Resistance, Junction-to-Lead (Note 2)	Ψ_{JCL}	8.6	°C/W
Thermal Resistance, Junction-to-Ambient (Note 2)	$R_{ hetaJA}$	80	°C/W
Thermal Resistance, Junction-to-Ambient (Note 3)	$R_{ hetaJA}$	237	°C/W

ELECTRICAL CHARACTERISTICS

Characteristic	Symbol	Value	Unit
Maximum Instantaneous Forward Voltage (Note 4) $ \begin{array}{l} (I_F=1.0 \text{ A}, T_J=25^{\circ}\text{C}) \\ (I_F=2.0 \text{ A}, T_J=25^{\circ}\text{C}) \\ (I_F=1.0 \text{ A}, T_J=125^{\circ}\text{C}) \\ (I_F=2.0 \text{ A}, T_J=125^{\circ}\text{C}) \end{array} $	V _F	0.55 0.65 0.47 0.58	V
Maximum Instantaneous Reverse Current (Note 4) (Rated dc Voltage, T _J = 25°C) (Rated dc Voltage, T _J = 125°C)	I _R	12 3	μA mA

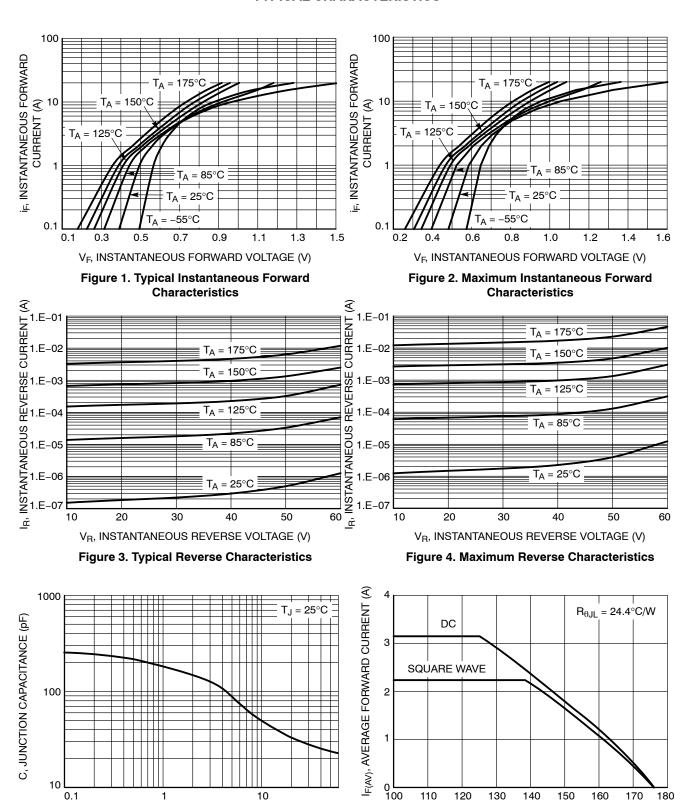
Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

- 2. Mounted with 700 mm² copper pad size (Approximately 1 in²) 1 oz FR4 Board.
- 3. Mounted with pad size approximately 20 mm² copper, 1 oz FR4 Board.
- 4. Pulse Test: Pulse Width \leq 380 μ s, Duty Cycle \leq 2.0%.

^{1.} The heat generated must be less than the thermal conductivity from Junction–to–Ambient: $dP_D/dT_J < 1/R_{\theta JA}$.

NRVTS2H60ESF, NRVTSM260EV2

TYPICAL CHARACTERISTICS



V_R, REVERSE VOLTAGE (V) Figure 5. Typical Junction Capacitance

10

0.1

T_C, CASE TEMPERATURE (°C) Figure 6. Current Derating

140

150

160

170

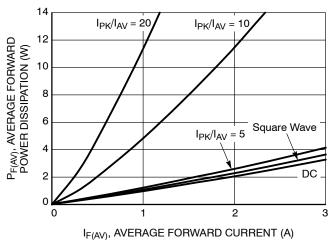
180

130

110

NRVTS2H60ESF, NRVTSM260EV2

TYPICAL CHARACTERISTICS



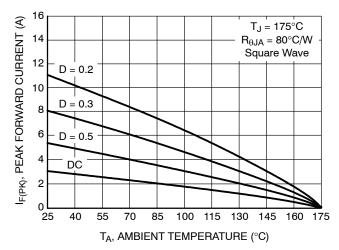
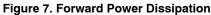


Figure 8. Forward Current Derating of Ambient Temperature



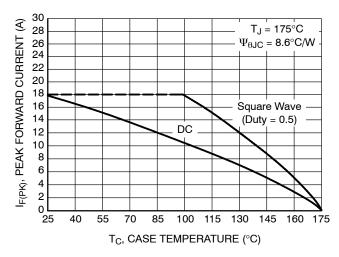


Figure 9. Forward Current Derating of Case **Temperature**

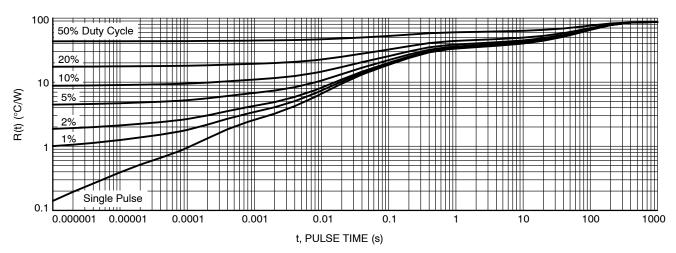
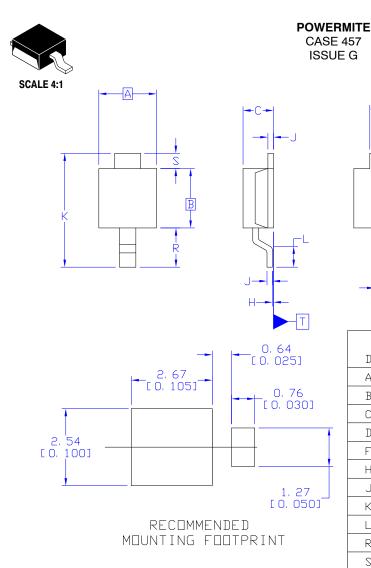


Figure 10. Thermal Characteristics

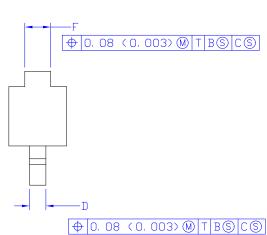


DATE 12 JAN 2022



GENERIC

MARKING DIAGRAMS*



	MILLIMETERS		INCHES	
DIM	MIN.	MAX.	MIN.	MAX.
А	1. 75	2, 05	0, 069	0. 081
В	1. 75	2. 18	0, 069	0, 086
С	0. 85	1. 15	0. 033	0. 045
D	0. 40	0. 69	0. 016	0. 027
F	0. 70	1. 00	0. 028	0. 039
Н	-0. 05	0. 10	-0. 002	0. 004
J	0.10	0, 25	0. 004	0.010
К	3, 60	3, 90	0.142	0. 154
L	0, 50	0, 80	0, 020	0. 031
R	1. 20	1, 50	0. 047	0, 059
S	0, 50 REF		0.019 REF	

NOTES:

- DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
- 2. CONTROLLING DIMENSION: MILLIMETERS

STYLE 2:

CATHODE

2. ANODE

3. DIMENSION & APPLIES TO PLATED TERMINAL AND IS MEASURED BETWEEN 0.15 AND 0.30mm FROM THE TERMINAL TIP.

PIN 1. ANODE OR CATHODE

2. CATHODE OR ANODE (BI-DIRECTIONAL)

IT NI IN	ARER:	00ASB140E2	C	Electronic versions
	STYLE	3 .	= Pb-Free Pa	ckage
_		<u> </u>	= Date Code	
\neg		XX	X = Specific Dev	ice Code
1	M XXX■	2		*
\Box	M			
1		STYLE 2		2.
				STYLE 1: PIN 1. (

XXX.

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

DOCUMENT NUMBER:	98ASB14853C	Electronic versions are uncontrolled except when accessed directly from the Document F Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.	
DESCRIPTION:	POWERMITE		PAGE 1 OF 1

onsemi and ONSemi are trademarks of Semiconductor Components Industries, LLC dba onsemi or its subsidiaries in the United States and/or other countries. onsemi reserves the right to make changes without further notice to any products herein. onsemi makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. onsemi does not convey any license under its patent rights nor the rights of others.

STYLE

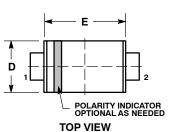
STYLE 3:

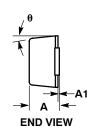
PIN 1. ANODE 2. CATHODE

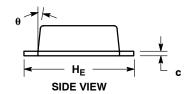


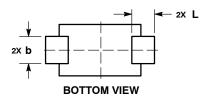
SOD-123FL **CASE 498** ISSUE D

DATE 10 MAY 2013

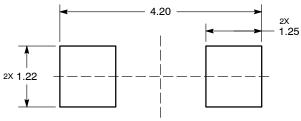








RECOMMENDED SOLDERING FOOTPRINT*



DIMENSIONS: MILLIMETERS

NOTES:

- ES:
 DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 CONTROLLING DIMENSION: MILLIMETER.
 DIMENSIONS A AND B DO NOT INCLUDE MOLD FLASH.
 DIMENSIONS D AND J ARE TO BE MEASURED ON FLAT SECTION
 OF THE LEAD: BETWEEN 0.10 AND 0.25 MM FROM THE LEAD TIP.

	MILLIMETERS		INCHES			
DIM	MIN	NOM	MAX	MIN	NOM	MAX
Α	0.90	0.95	0.98	0.035	0.037	0.039
A1	0.00	0.05	0.10	0.000	0.002	0.004
b	0.70	0.90	1.10	0.028	0.035	0.043
С	0.10	0.15	0.20	0.004	0.006	0.008
D	1.50	1.65	1.80	0.059	0.065	0.071
E	2.50	2.70	2.90	0.098	0.106	0.114
L	0.55	0.75	0.95	0.022	0.030	0.037
HE	3.40	3.60	3.80	0.134	0.142	0.150
θ	0°	-	8°	0°	-	8°

GENERIC MARKING DIAGRAM*



XXX = Specific Device Code

= Date Code

= Pb-Free Package

(Note: Microdot may be in either location)

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ■", may or may not be present.

DOCUMENT NUMBER:	98AON11184D	Electronic versions are uncontrolled except when accessed directly from the Document Repo Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.		
DESCRIPTION:	SOD-123FL		PAGE 1 OF 1	

ON Semiconductor and unare trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. ON Semiconductor does not convey any license under its patent rights nor the rights of others.

^{*}For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

onsemi, ONSEMI, and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "onsemi" or its affiliates and/or subsidiaries in the United States and/or other countries. onsemi owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of onsemi's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. Onsemi reserves the right to make changes at any time to any products or information herein, without notice. The information herein is provided "as-is" and onsemi makes no warranty, representation or guarantee regarding the accuracy of the information, product features, availability, functionality, or suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using onsemi products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications provided by onsemi. "Typical" parameters which may be provided in onsemi data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. onsemi does not convey any license under any of its intellectual property rights nor the rights of others. onsemi products are not designed, intended, or authorized for use as a critical component in life support systems or any EDA class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer pu

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT: Email Requests to: orderlit@onsemi.com

onsemi Website: www.onsemi.com

TECHNICAL SUPPORT North American Technical Support: Voice Mail: 1 800-282-9855 Toll Free USA/Canada Phone: 011 421 33 790 2910

Europe, Middle East and Africa Technical Support:

Phone: 00421 33 790 2910

For additional information, please contact your local Sales Representative

X-ON Electronics

Largest Supplier of Electrical and Electronic Components

Click to view similar products for Schottky Diodes & Rectifiers category:

Click to view products by ON Semiconductor manufacturer:

Other Similar products are found below:

MA4E2039 D1FH3-5063 MBR0530L-TP MBR10100CT-BP MBR1545CT MMBD301M3T5G RB160M-50TR RB551V-30

BAS16E6433HTMA1 BAT 54-02LRH E6327 NSR05F40QNXT5G NTE555 JANS1N6640 SB07-03C-TB-H SB1003M3-TL-W SK310-T

SK32A-LTP SK34B-TP SS3003CH-TL-E GA01SHT18 CRS10I30A(TE85L,QM MA4E2501L-1290 MBRB30H30CT-1G SB007-03C-TB-E SK32A-TP SK33B-TP SK38B-TP NRVBM120LT1G NTE505 NTSB30U100CT-1G SS15E-TP VS-6CWQ10FNHM3 ACDBA1100LR-HF ACDBA1200-HF ACDBA2100-HF ACDBA3100-HF CDBQC0530L-HF ACDBA340-HF ACDBA260LR-HF

ACDBA1100-HF SK310B-TP MA4E2502L-1246 MA4E2502H-1246 NRVBM120ET1G NSR01L30MXT5G NTE573 NTE6081 SB560 PMAD1108-LF